

**/ Descriptions**

TO-220          N      MOS          N-CHANNEL MOSFET in a TO-220 Plastic Package.

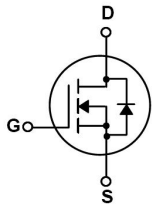
**/ Features**

Fast switching, low on resistance, low gate charge, low reverse transfer capacitances.

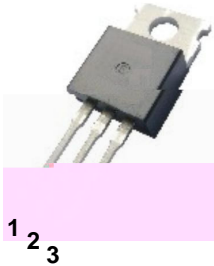
**/ Applications**

Used in various power switching circuit for system miniaturization and higher efficiency.

**/ Equivalent Circuit**



**/ Pinning**



PIN1 G          PIN 2 D          PIN 3 S

**/ h<sub>FE</sub> Classifications & Marking**

See Marking Instructions.

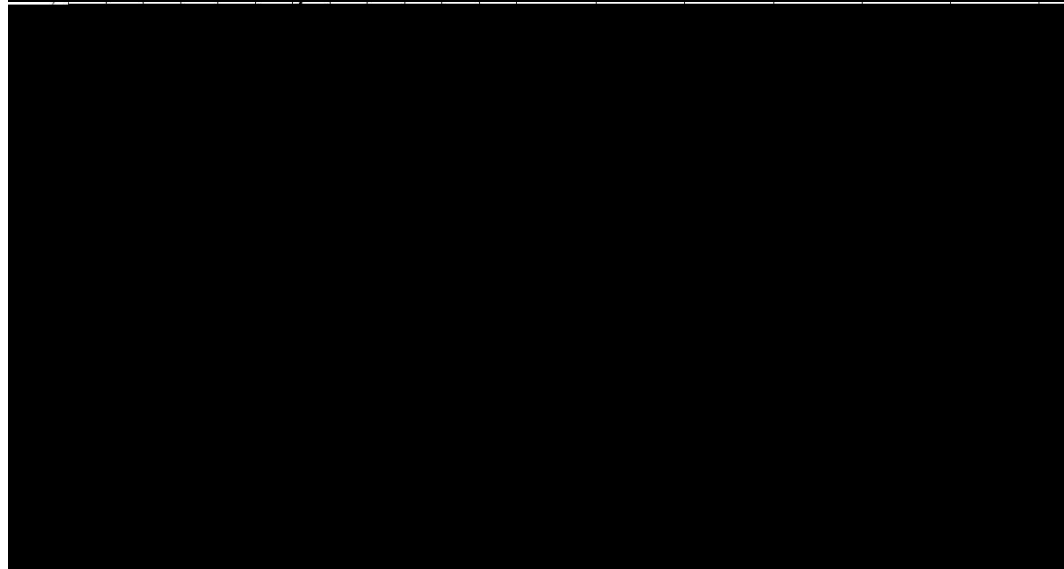
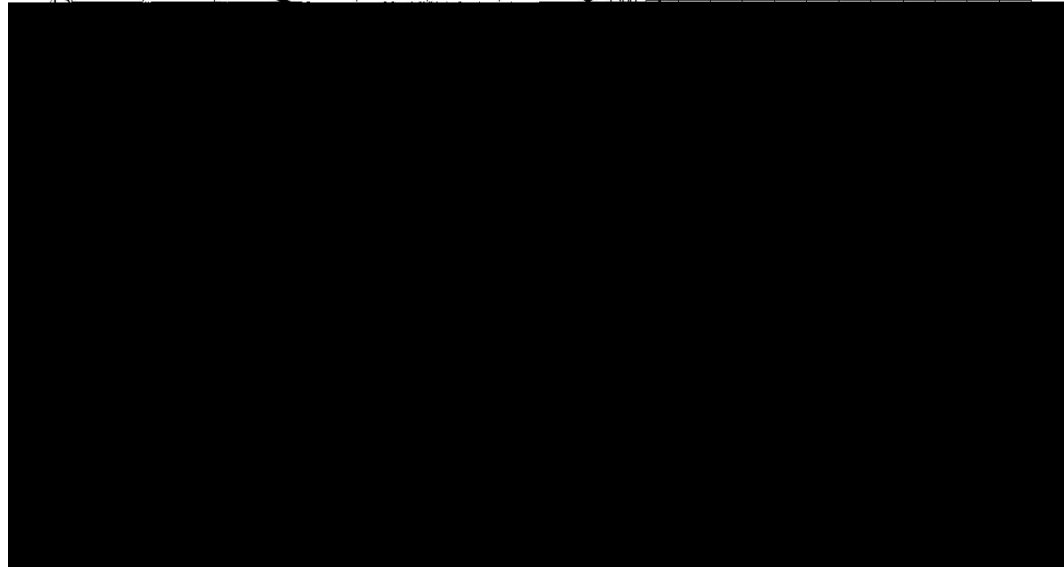
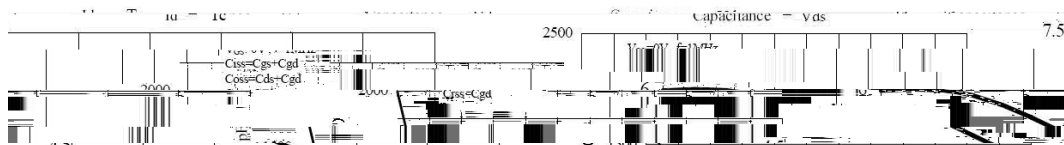
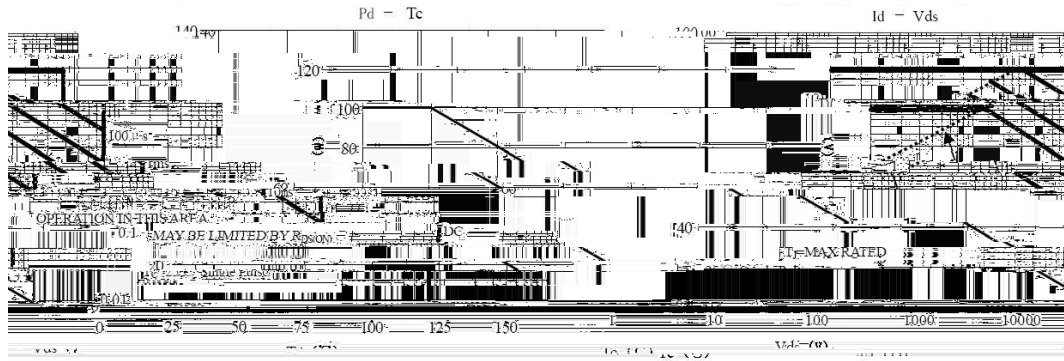
**/ Absolute Maximum Ratings(Ta=25 )**

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	700	V
Drain Current	$I_D(T_c=25)$	6.0	A
Drain Current	$I_D(T_c=100)$	3.6	A
Drain Current - Pulsed	$I_{DM}$	24	A
Gate-Source Voltage	$V_{GS}$	±30	V
Single Pulsed Avalanche Energy	$E_{AS}$	185	mJ
Repetitive Avalanche Energy	$E_{AR}$	20	mJ
Avalanche Current	$I_{AR}$	3.3	A
Power Dissipation	$P_D(T_c=25)$	100	W
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	
Junction-to-Case	$R_{JC}$	1.25	/W
Junction-to-Ambient	$R_{JA}$	62	/W

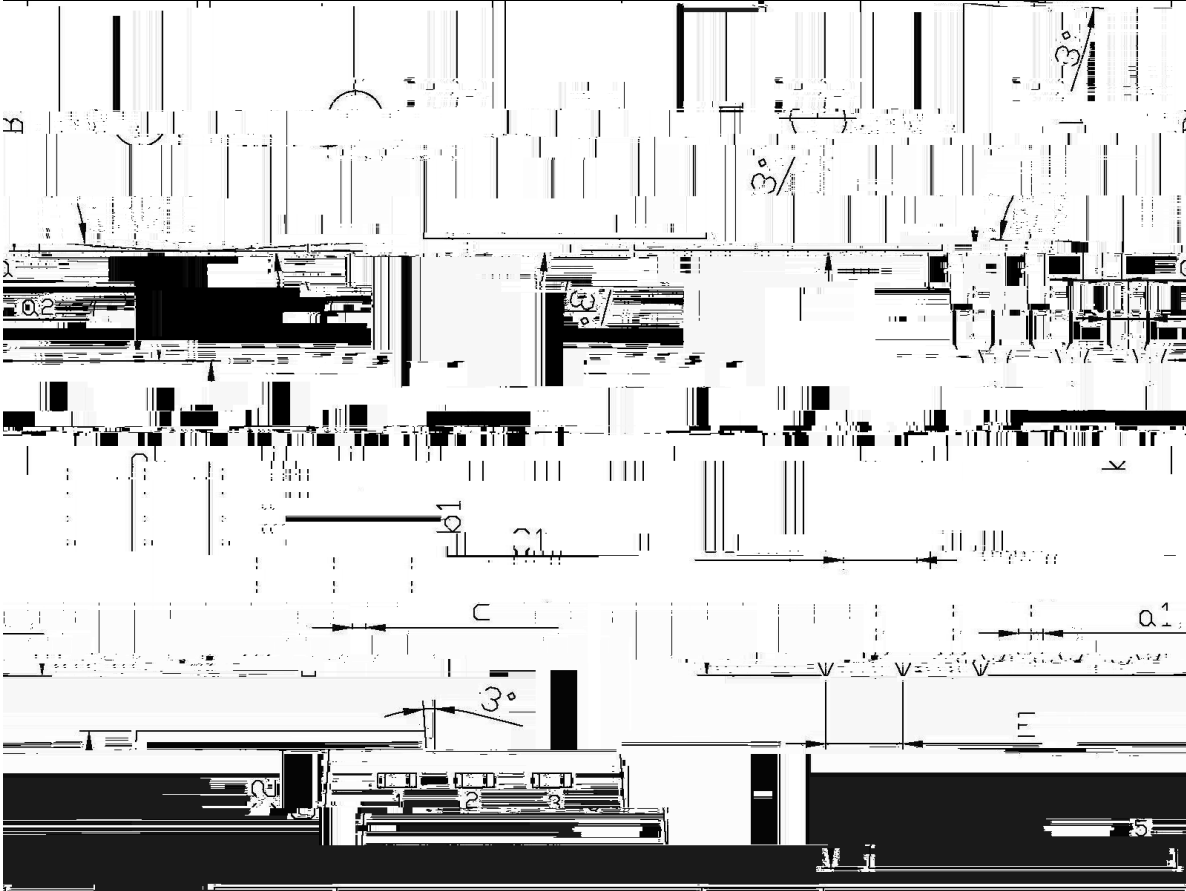
**/ Electrical Characteristics(Ta=25 )**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V$ $I_D=250$ A	700			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=700V$ $V_{GS}=0V$			1	A
		$V_{DS}=560V$ $T_a=125$			100	A
Gate-Body Leakage Current, Forward	$I_{GSS}$	$V_{GS}=\pm 20V$ $V_{DS}=0V$			±10	A
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250$ A	2.0		4.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=3.0A$		1.35	1.6	
Forward Transconductance	$g_{FS}$	$V_{DS}=15V$ $I_D=3.0A$		5.0		S
Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V$ $I_S=6.0A$			1.5	V
Input Capacitance	$C_{iss}$	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		938		pF
Output Capacitance	$C_{oss}$			87.8		pF
Reverse Transfer Capacitance	$C_{rss}$			8.2		pF
Turn-On Delay Time	$t_{d(on)}$				14.7	
Turn-On Rise Time	$t_r$	$V_{DD}=350V$ $R_G=25$ $I_D=6.0A$ $V_{GS}=10V$		26		ns
Turn-Off Delay Time	$t_{d(off)}$			68.4		ns
Turn-Off Fall Time	$t_f$			34.6		ns

/ Electrical Characteristic Curve

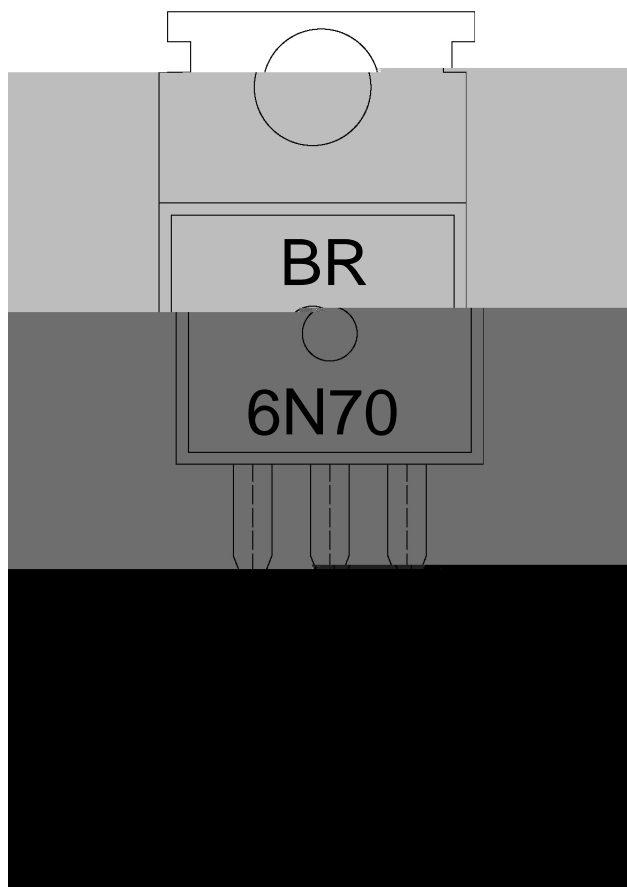


**/ Package Dimensions**



Dimensions in Millimeters				Dimensions in Millimeters			
Symbol	Min	Max	Symbol	Min	Max		
A	9.8	10.2	C	1.2	1.4		
B	15.7	16.1	D	6.3	6.7		
C	3.6	3.8	E	9.0	9.4		
D	1.2	1.4	F	0.2	0.3		
E	6.3	6.7	G	1.25	1.5		
F	9.0	9.4	H	0.2	0.3		
G	0.2	0.3	I	1.25	1.5		
H	1.25	1.5	J	0.2	0.3		
I	0.2	0.3	K	1.25	1.5		
J	0.2	0.3	L	0.2	0.3		
K	1.25	1.5	M	0.2	0.3		
L	0.2	0.3	N	0.2	0.3		
M	0.2	0.3	O	0.2	0.3		
N	0.2	0.3	P	0.2	0.3		
O	0.2	0.3	Q	0.2	0.3		
P	0.2	0.3	R	0.2	0.3		
Q	0.2	0.3	S	0.2	0.3		
R	0.2	0.3	T	0.2	0.3		
S	0.2	0.3	U	0.2	0.3		
T	0.2	0.3	V	0.2	0.3		
U	0.2	0.3	W	0.2	0.3		
V	0.2	0.3	X	0.2	0.3		
W	0.2	0.3	Y	0.2	0.3		
X	0.2	0.3	Z	0.2	0.3		
Y	0.2	0.3					
Z	0.2	0.3					

/ Marking Instructions



BR

- E .

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Note:

BR: Company Code

6N70: Product Type.

\*\*\*\*: Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- |   |        |            |   |
|---|--------|------------|---|
| 1 | 25 150 | 60 90sec;  | 1.Preheating:25~150 , Time:60~90sec.      |
| 2 | 255..5 | 5..0.5sec; | 2.Peak Temp.:255..5 , Duration:5..0.5sec. |
| 3 | 2 10   | /sec.      | 3. Cooling Speed: 2~10 /sec.              |

/ Resistance to Soldering Heat Test Conditions

270..5                      10..1 sec.                      Temp.:270±5                      Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	只袋	袋盒	只盒	盒箱	只箱	袋	盒	箱